

Datasheet

FS8205A

Dual N-Channel Enhancement Mode Power MOSFET

For Reference Only

Fortune Semiconductor Corporation
富晶電子股份有限公司
28F., No.27, Sec. 2, Zhongzheng E. Rd.,
Danshui Town, Taipei County 251, Taiwan
Tel. : 886-2-28094742
Fax : 886-2-28094874
www.ic-fortune.com

FSC,
Properties Only
For Reference Only

This manual contains new product information. **Fortune Semiconductor Corporation** reserves the rights to modify the product specification without further notice. No liability is assumed by **Fortune Semiconductor Corporation** as a result of the use of this product. No rights under any patent accompany the sale of the product

1. Features

1.1 Low on-resistance

- 1.1.1 $R_{DS(ON)} = 25 \text{ m}\Omega$ MAX. ($V_{GS} = 4.5V$, $I_D = 4A$)
- 1.1.2 $R_{DS(ON)} = 35 \text{ m}\Omega$ MAX. ($V_{GS} = 2.5V$, $I_D = 3A$)

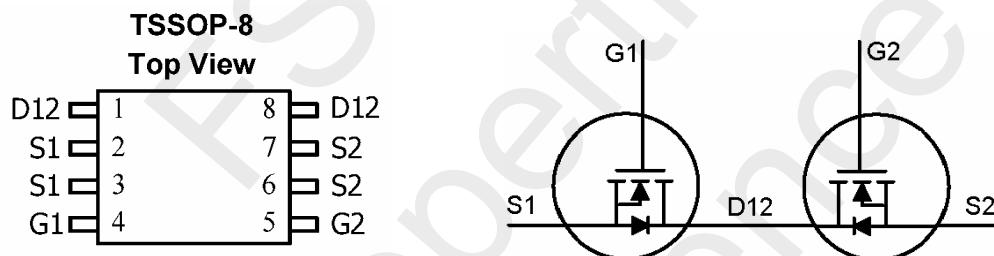
2. Applications

- Li-ion battery management applications

3. Ordering Information

Product Number	Description	Package Type	Quantity/Reel
FS8205A	TSSOP8 package version	TSSOP-8	3,000

4. Pin Assignment



5. Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	20	V
VGS	Gate-Source Voltage	± 12	V
ID @ TA = 25°C	Continuous Drain Current3	6	A
ID @ TA = 70°C	Continuous Drain Current3	5	A
IDM	Pulsed Drain Current1	25	A
PD @ TA = 25°C	Total Power Dissipation	1	W
	Linear Derating Factor	0.008	W/°C
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

6. Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Thermal Resistance Junction-ambient3	Max. 125	°C/W

7. Electrical Characteristics

Electrical Characteristics @ $T_j = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}} = 0\text{V}, I_{\text{D}} = 250\mu\text{A}$	20	-	-	V
$\Delta \text{BV}_{\text{DSS}}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to 25°C , $I_{\text{D}}=1\text{mA}$	-	0.1	-	$\text{V}/^\circ\text{C}$
$R_{\text{DS}(\text{ON})}$	Static Drain-Source On-Resistance ²	$V_{\text{GS}} = 4.5\text{V}, I_{\text{D}} = 4\text{A}$	-	21	25	$\text{m}\Omega$
		$V_{\text{GS}} = 2.5\text{V}, I_{\text{D}} = 3\text{A}$	-	27	35	$\text{m}\Omega$
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250\mu\text{A}$	0.5	-	1.0	V
I_{DSS}	Drain-Source Leakage Current ($T_j = 25^\circ\text{C}$)	$V_{\text{DS}} = 20\text{V}, V_{\text{GS}} = 0\text{V}$	-	-	1	μA
	Drain-Source Leakage Current ($T_j = 70^\circ\text{C}$)	$V_{\text{DS}} = 20\text{V}, V_{\text{GS}} = 0\text{V}$	-	-	25	μA
I_{GSS}	Gate-Source Leakage	$V_{\text{GS}} = \pm 10\text{V}$	-	-	± 10	μA

8. Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_S	Continuous Source Current (Body Diode)	$V_D = V_G = 0\text{V}, V_S = 1.2\text{V}$	-	-	0.83	A
V_{SD}	Forward On Voltage ²	$T_j = 25^\circ\text{C}, I_S = 1.25\text{A}, V_{\text{GS}} = 0\text{V}$	-	-	1.2	V

Notes :

1. Pulse width limited by Max. junction temperature.
2. Pulse width $\leq 300\text{us}$, duty cycle $\leq 2\%$.
3. Surface mounted on 1 in² copper pad of FR4 board ; $208^\circ\text{C}/\text{W}$ when mounted on Min. copper pad.

9. Typical Characteristics

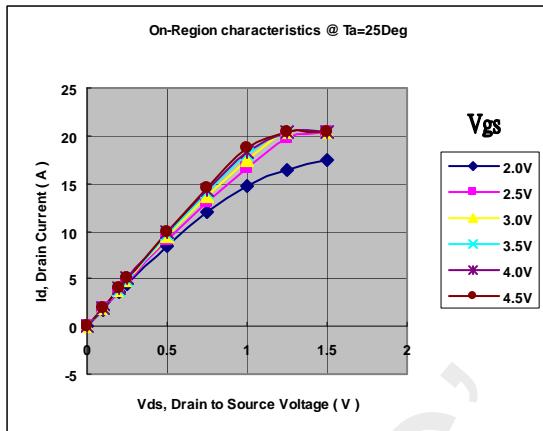


Fig 1. Typical Output Characteristics

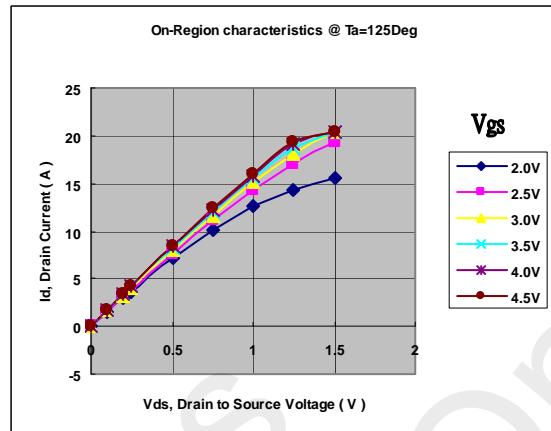


Fig 2. Typical Output Characteristics

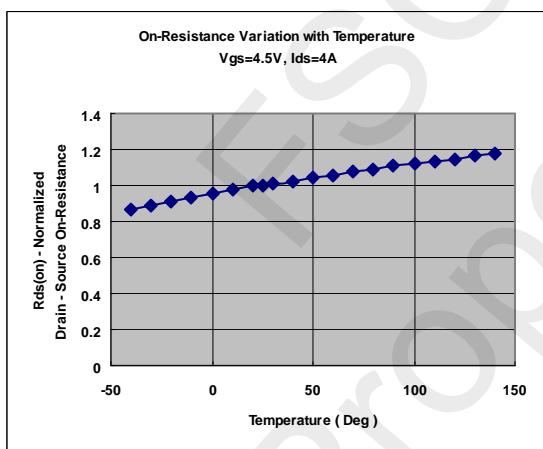


Fig 3. Normalized On-Resistance

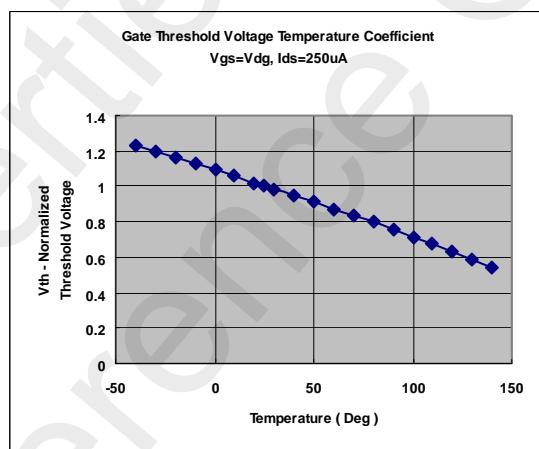


Fig 4. Gate Threshold Variation with Temperature

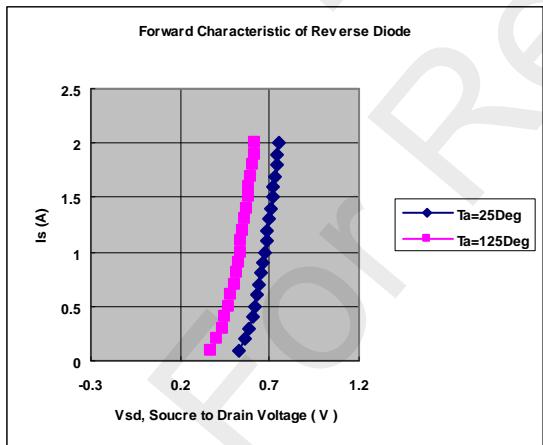
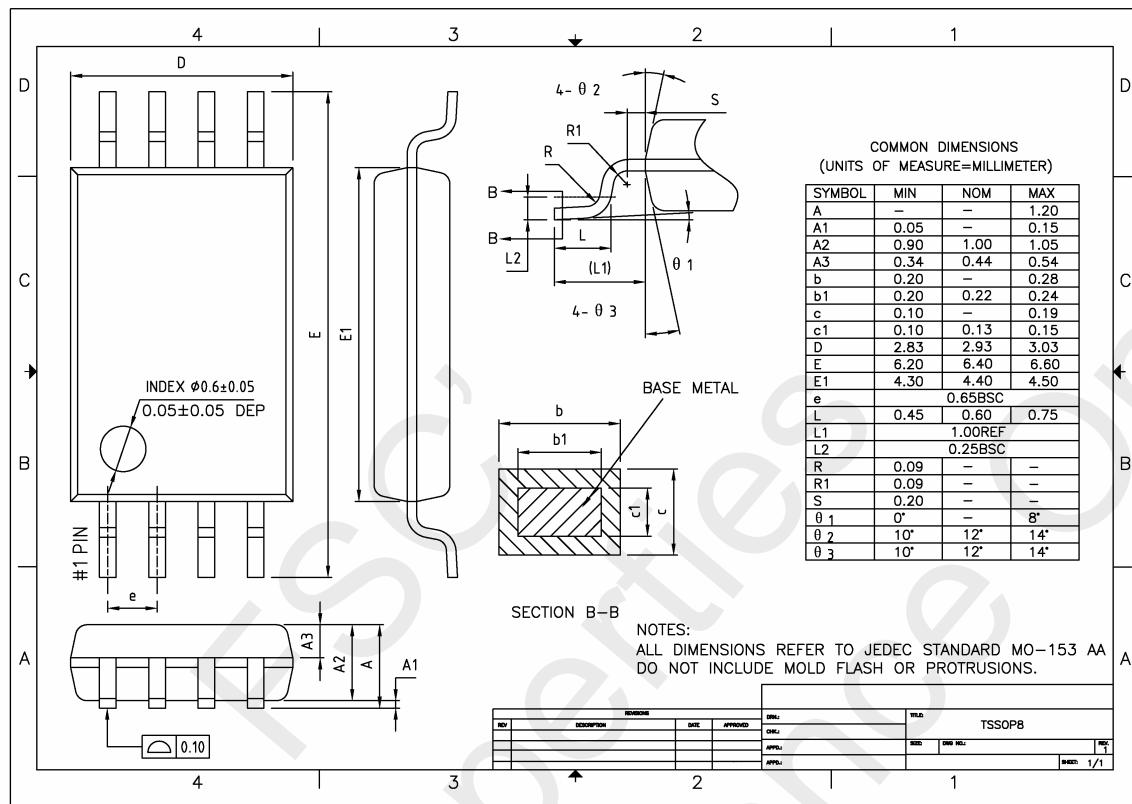


Fig 5. Forward Characteristic of Reverse Diode

10. Package Information



11. Revision History

Version	Date	Page	Description
1.0	2009/02/10	-	Version 1.0 released
1.1	2009/04/28	3~4	Rds25 TYP 25mohm MAX 32mohm Rds45 TYP 20mohm MAX 25mohm ID @TA = 25°C 6A ID @TA = 70°C 5A ID pulse 300 μ s 25A
1.2	2009/08/04	3~4	Rds25 TYP 27mohm MAX 35mohm Rds45 TYP 21mohm MAX 25mohm Rds25 ID : 3A Rds45 ID : 4A

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Fortune manufacturer:

Other Similar products are found below :

[614233C](#) [648584F](#) [MCH3443-TL-E](#) [MCH6422-TL-E](#) [FDPF9N50NZ](#) [FW216A-TL-2W](#) [FW231A-TL-E](#) [APT5010JVR](#) [NTNS3A92PZT5G](#)
[IRF100S201](#) [JANTX2N5237](#) [2SK2464-TL-E](#) [2SK3818-DL-E](#) [FCA20N60_F109](#) [FDZ595PZ](#) [STD6600NT4G](#) [FSS804-TL-E](#) [2SJ277-DL-E](#)
[2SK1691-DL-E](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [MCH6646-TL-E](#) [TPCC8103,L1Q\(CM](#) [367-8430-0972-503](#) [VN1206L](#) [424134F](#)
[026935X](#) [051075F](#) [SBVS138LT1G](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [751625C](#) [873612G](#) [IRF7380TRHR](#) [IPS70R2K0CEAKMA1](#)
[RJK60S3DPP-E0#T2](#) [RJK60S5DPK-M0#T0](#) [APT5010JVFR](#) [APT12031JFLL](#) [APT12040JVR](#) [DMN3404LQ-7](#) [NTE6400](#) [JANTX2N6796U](#)
[JANTX2N6784U](#) [JANTXV2N5416U4](#) [SQM110N05-06L-GE3](#) [SIHF35N60E-GE3](#) [2SK2614\(TE16L1,Q\)](#)